



AL422B Data Sheets

(Revision V1.5)

Amendments (Since April 2, 1999)

05-13-99	DC/AC characteristics (including current consumption) updated.
07-02-99	Pinout diagram (5.0) and DC external load (7.4) modified.
08-03-99	Description about TST pin added in sections 6.0 & 8.1.
09-02-99	8.3.2 Rewritten.
10-26-99	Capacitance provided in the AC characteristics section.
12-15-99	Remove TST pin restriction.
01-18-01	1. Revised section “8.3.2 Read Enable during Reset Cycles” to “8.3.2 The Proper Manipulation of FIFO Access”. 2. Add section “8.3.3 Single Field Write with Multiple Read Operation” 3. Add section “8.3.4 One Field Delay Line (The Old Data Read)”
02-28-02	Address and version update
03-20-02	Correct Pin-out diagram
02-20-03	Company Contact Information updated
04-27-04	1. Revised “5V or 3.3V power supply” in section “2.0 Features” 2. Revised “+5V/+3.3 volt” in section “4.0 Ordering Information” 3. Revised “5V or 3.3V” in section “6.0 Pin Description” 4. Revised section “7.0 Electrical Characteristics” 5. Revised section “8.2 5V and 3.3V application”
05-11-04	Include PB-free package “AL422B-PBF”

AL422B 3M-Bits FIFO Field Memory

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1.0 Description

The AL422 consists of 3M-bits of DRAM, and is configured as 393,216 words x 8 bit FIFO (first in first out). The interface is very user-friendly since all complicated DRAM operations are already managed by the internal DRAM controller.

Current sources of similar memory (field memory) in the market provide limited memory size which is only enough for holding one TV field, but not enough to hold a whole PC video frame which normally contains 640x480 or 720x480 bytes. The AverLogic AL422 provides 50% more memory to support high resolution for digital PC graphics or video applications. The 50% increase in speed also expands the range of applications.

2.0 Features

- 384K (393,216) x 8 bits FIFO organization
- Support VGA, CCIR, NTSC, PAL and HDTV resolutions
- Independent read/write operations (different I/O data rates acceptable)
- High speed asynchronous serial access
- Read/write cycle time: 20ns
- Access time: 15ns
- Output enable control (data skipping)
- Self refresh
- 5V or 3.3V power supply
- Standard 28-pin SOP package

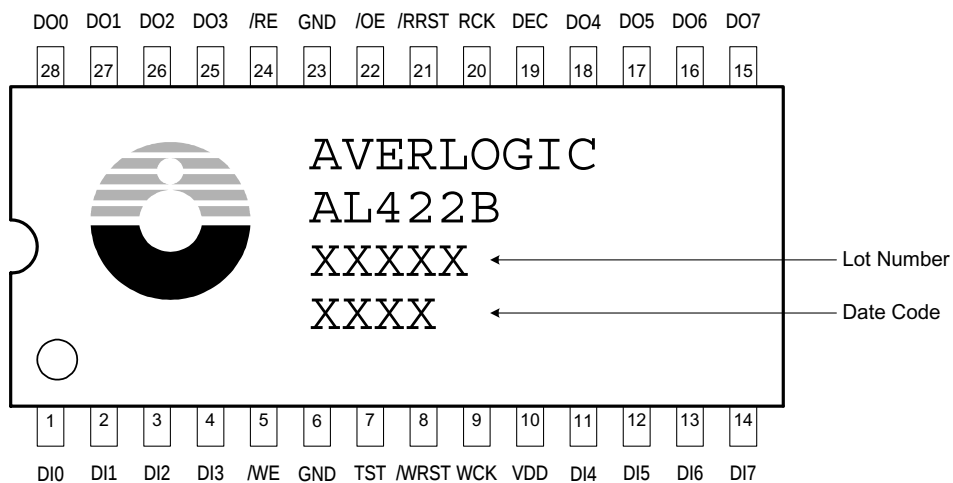
3.0 Applications

- Multimedia systems
- Video capture systems
- Video editing systems
- Scan rate converters
- TV's picture in picture feature
- Time base correction (TBC)
- Frame synchronizer
- Digital video camera
- Buffer for communications systems

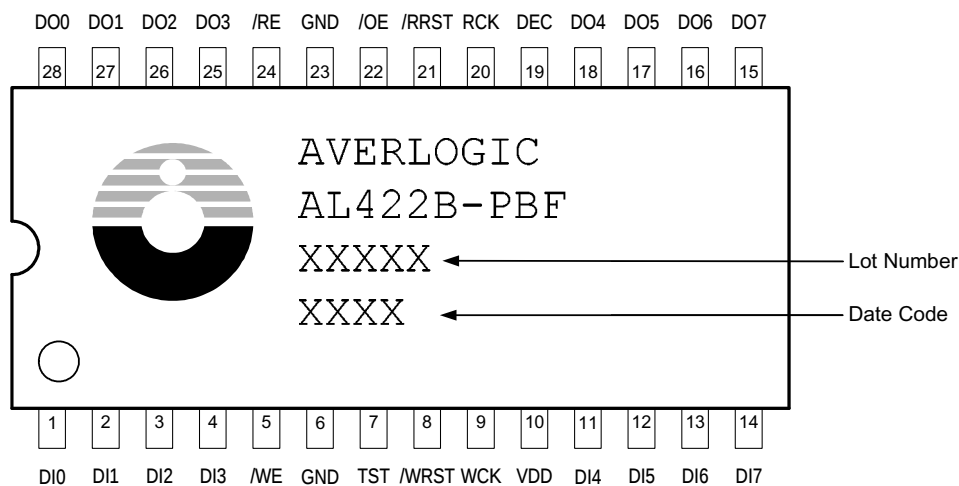
4.0 Ordering Information

Part number	Package	Power Supply	Status
AL422B	28-pin plastic SOP	+5/+3.3 volt	Shipping
AL422B-PBF	28-pin plastic SOP	+5/+3.3 volt	Shipping

5.0 Pinout Diagram



AL422-04 422B pinout diagram



AL422B-PBF pinout diagram

Note: "PBF" to indicate it is Pb free package.

6.0 Pin Description

Pin name	Pin #	I/O type	Function
DI0~DI7	1~4, 11~14	input	Data input
WCK	9	Input	Write clock
/WE	5	Input (active low)	Write enable
/WRST	8	Input (active low)	Write reset
DO0~DO7	15~18, 25~28	Output (tristate)	Data output
RCK	20	Input	Read clock
/RE	24	Input (active low)	Read enable
/RRST	21	Input (active low)	Read reset
/OE	22	Input (active low)	Output enable
TST	7	Input	Test pin (pulled-down)*
VDD	10		5V or 3.3V
DEC/VDD	19		Decoupling cap input
GND	6, 23		Ground

7.0 Electrical Characteristics

7.1 Absolute Maximum Ratings

Parameter	Ratings		Unit
	3.3V application	5V application	
V _{DD} Supply Voltage	-1.0 ~ +4.5	-1.0 ~ +7.0	V
V _P Pin Voltage	-1.0 ~ +5.5	-1.0 ~ V _{DD} +0.5	V
I _O Output Current	-20 ~ +20	-20 ~ +20	mA
T _{AMB} Ambient Op. Temperature	0 ~ +70	0 ~ +70	°C
T _{stg} Storage temperature	-55 ~ +125	-55 ~ +125	°C

7.2 Recommended Operating Conditions

Parameter		3.3V application		5V application		Unit
		Min	Max	Min	Max	
V _{DD}	Supply Voltage	+3.0	+3.6	+4.5	+5.25	V
V _{IH}	High Level Input Voltage	+2.0	+5.5	+3.0	V _{DD} +0.5	V
V _{IL}	Low Level Input Voltage	-1.0	+0.8	-1.0	+0.8	V

7.3 DC Characteristics

(V_{DD} = 5V or 3.3V, V_{SS} = 0V, T_{AMB} = 0 to 70°C)

Parameter		3.3V application			5V application			Unit
		Min	Typ	Max	Min	Typ	Max	
I _{DD}	Operating Current @20MHz	-	33	-	-	50	-	mA
I _{DD}	Operating Current @30MHz	-	45	-	-	66	-	mA
I _{DD}	Operating Current @40MHz	-	57	-	-	82	-	mA
I _{DD}	Operating Current @50MHz	-	68	-	-	97	-	mA
I _{DDS}	Standby Current	-	7	-	-	12	-	mA
V _{OH}	Hi-level Output Voltage	0.7V _{DD}	-	V _{DD}	+3.0	-	V _{DD}	V
V _{OL}	Lo-level Output Voltage	-	-	+0.4	-	-	+0.4	V
I _{LI}	Input Leakage Current	-10	-	+10	-10	-	+10	μA
I _{LO}	Output Leakage Current	-10	-	+10	-10	-	+10	μA

7.4 AC Characteristics

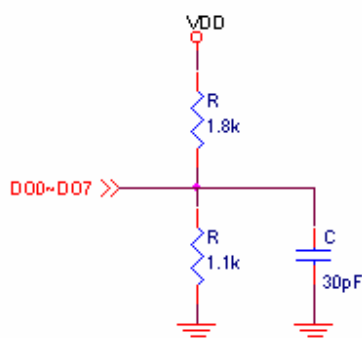
(V_{DD} = 5V or 3.3V, V_{SS} = 0V, T_{AMB} = 0 to 70°C)

Parameter		3.3V application		5V application		Unit
		Min	Max	Min	Max	
T _{WC}	WCK Cycle Time	20	1000	20	1000	ns
T _{WPH}	WCK High Pulse Width	7	-	7	-	ns
T _{WPL}	WCK Low Pulse Width	7	-	7	-	ns
T _{RC}	RCK Cycle Time	20	1000	20	1000	ns
T _{RPH}	RCK High Pulse Width	7	-	7	-	ns
T _{RPL}	RCK Low Pulse Width	7	-	7	-	ns
T _{AC}	Access Time	-	15	-	15	ns
T _{OH}	Output Hold Time	4	-	4	-	ns

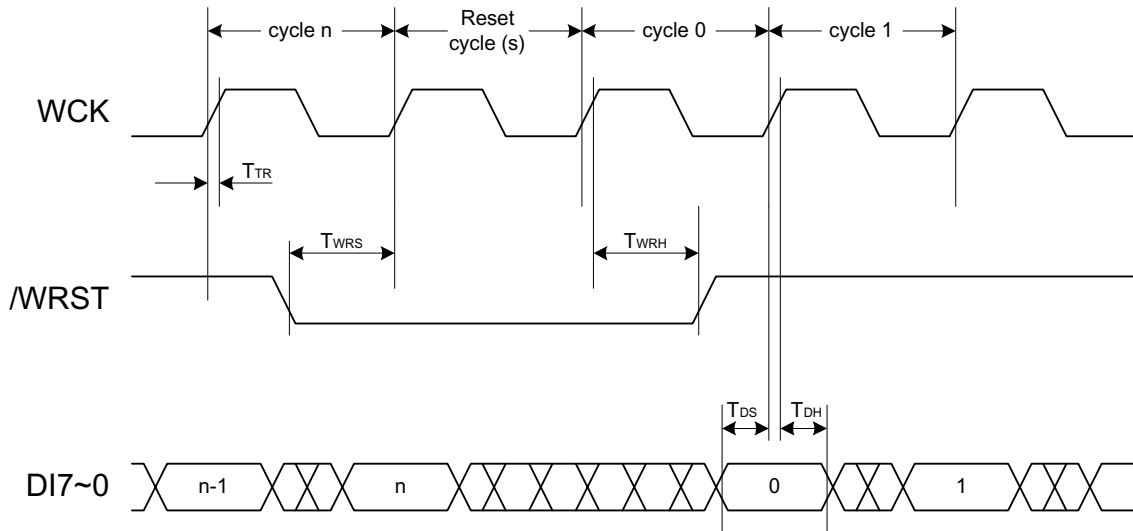
T_{HZ}	Output High-Z Setup Time	3	15	4	15	ns
T_{LZ}	Output Low-Z Setup Time	3	15	4	15	ns
T_{WRS}	/WRST Setup Time	5	-	6	-	ns
T_{WRH}	/WRST Hold Time	2	-	3	-	ns
T_{RRS}	/RRST Setup Time	5	-	6	-	ns
T_{RRH}	/RRST Hold Time	2	-	3	-	ns
T_{DS}	Input Data Setup Time	5	-	6	-	ns
T_{DH}	Input Data Hold Time	2	-	3	-	ns
T_{WES}	/WE Setup Time	5	-	6	-	ns
T_{WEH}	/WE Hold Time	2	-	3	-	ns
T_{WPW}	/WE Pulse Width	10	-	10	-	ns
T_{RES}	/RE Setup Time	5	-	6	-	ns
T_{REH}	/RE Hold Time	2	-	3	-	ns
T_{RPW}	/RE Pulse Width	10	-	10	-	ns
T_{OES}	/OE Setup Time	5	-	6	-	ns
T_{OEH}	/OE Hold Time	2	-	3	-	ns
T_{OPW}	/OE Pulse Width	10	-	10	-	ns
T_{TR}	Transition Time	2	20	3	20	ns
C_I	Input Capacitance	-	7	-	7	pF
C_O	Output Capacitance	-	7	-	7	pF

- Input voltage levels are defined as $V_{IH}=3.0V$ and $V_{IL}=0.4V$.
- The read address needs to be at least 128 cycles after the write address.

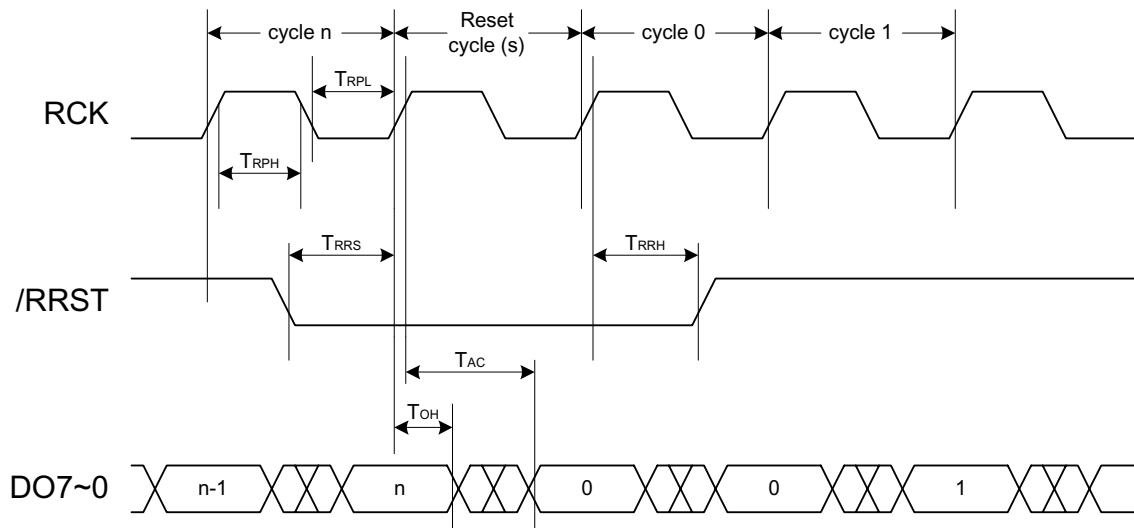
DO external load:



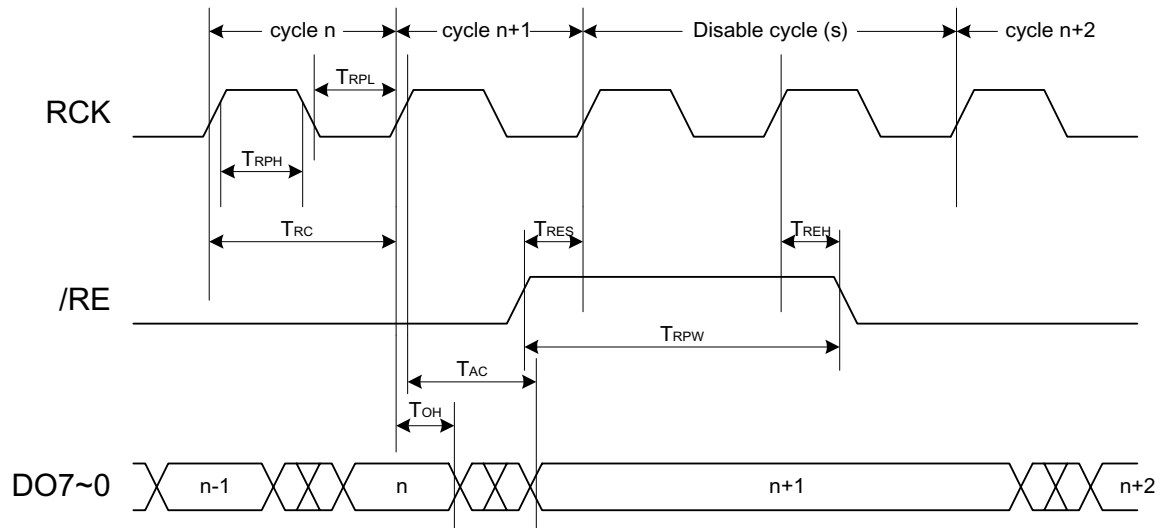
7.5 Timing Diagrams



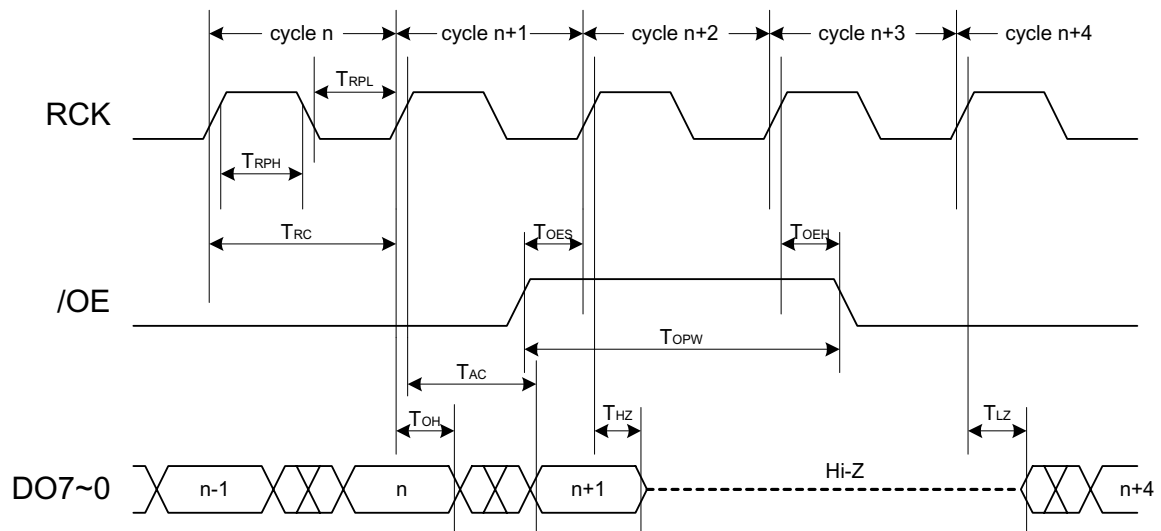
AL422-05 Write Cycle Timing (Write Reset)



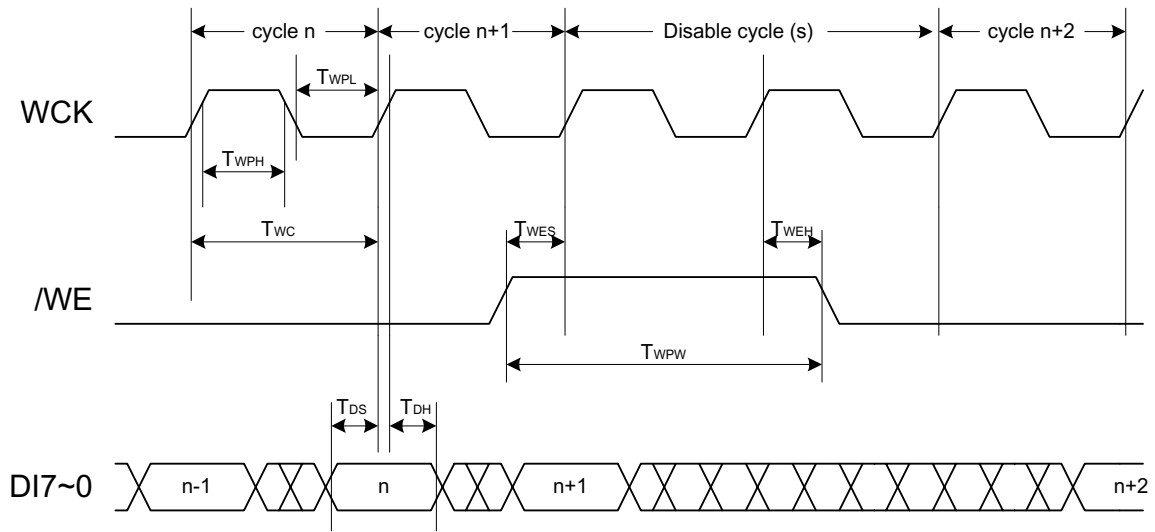
AL422-07 Read Cycle Timing (Read Reset)



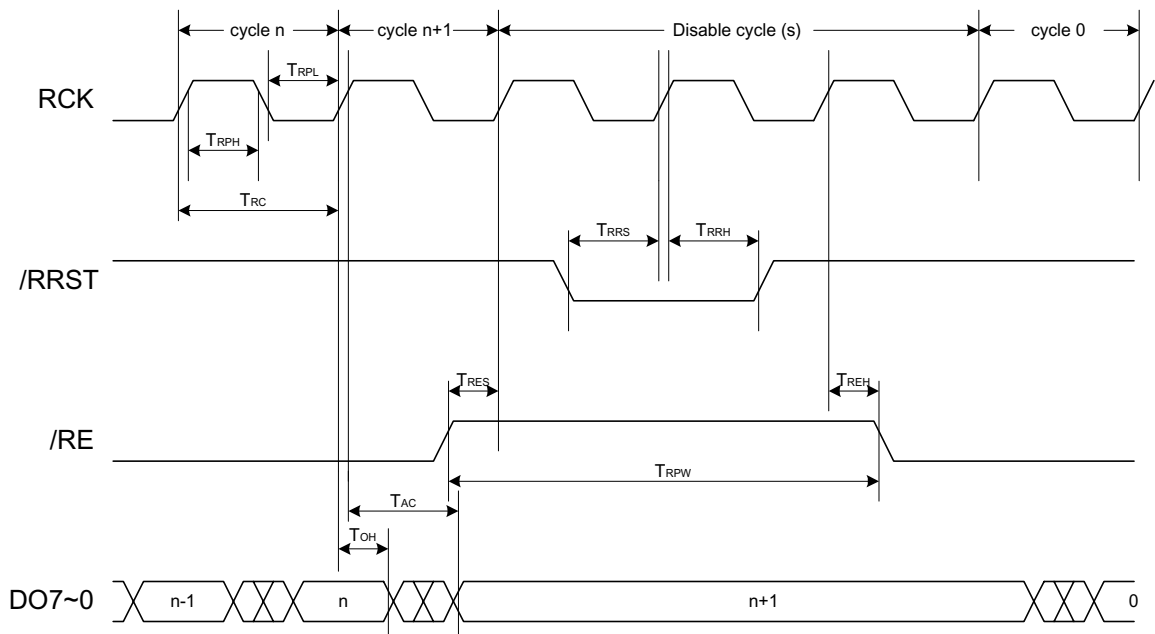
AL422-08 Read Cycle Timing (Read Enable)



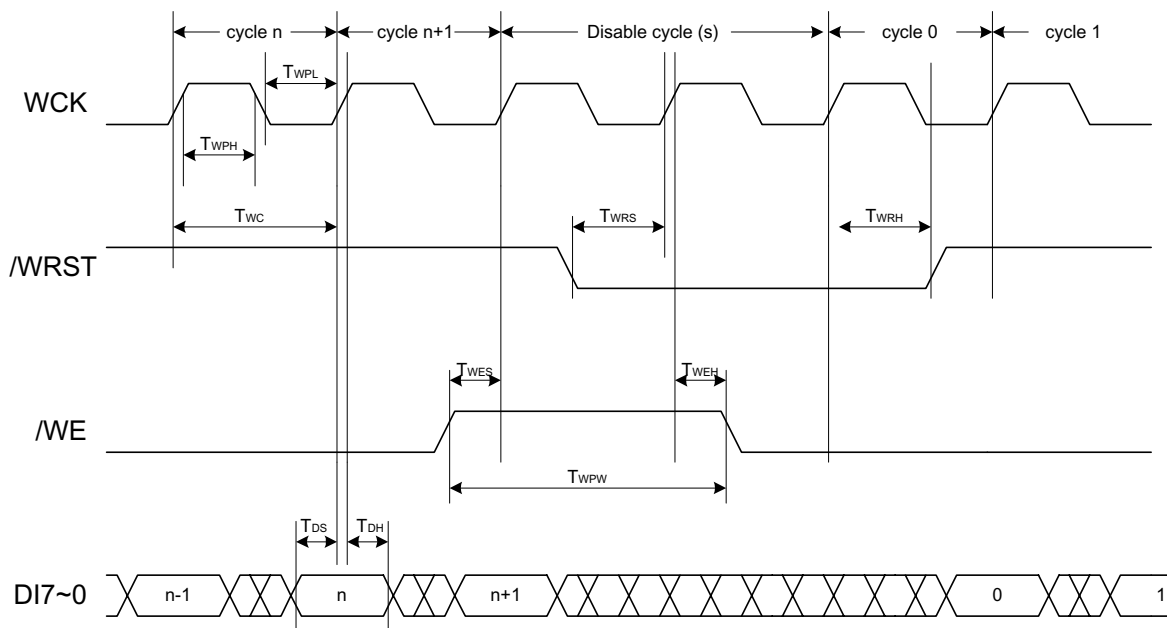
AL422-09 Read Cycle Timing (Output Enable)



AL422-06 Write Cycle Timing (Write Enable)



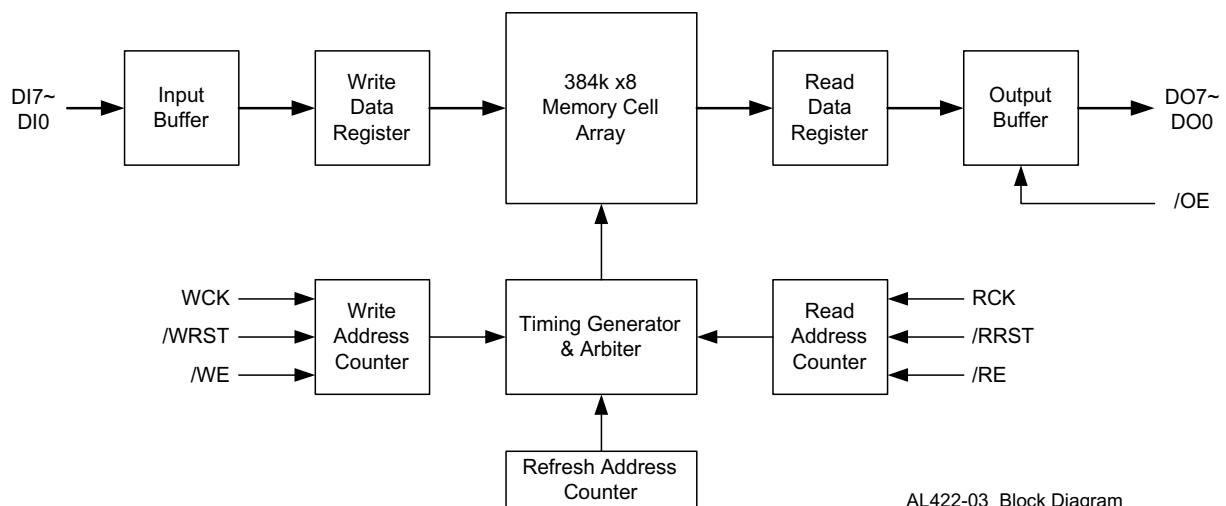
AL422-14 Read Cycle Timing (RE, RRST)



AL422-15 Write Cycle Timing (WE, WRST)

8.0 Functional Description

The AL422 is a video frame buffer consisting of DRAM that works like a FIFO which is long enough to hold up to 819x480 bytes of picture information and fast enough to operate at 50MHz. The functional block diagram is as follows:



The I/O pinouts and functions are described as follows:

DI7~DI0 Data Input: Data is input on the rising edge of the cycle of WCK when /WE is pulled low (enabled).

DO7~DO0 Data Output: Data output is synchronized with the RCK clock. Data is obtained at the rising edge of the RCK clock when /RE is pulled low. The access time is defined from the rising edge of the RCK cycle.

WCK Write Clock Input: The write data input is synchronized with this clock. Write data is input at the rising edge of the WCK cycle when /WE is pulled low (enabled). The internal write address pointer is incremented automatically with this clock input.

RCK Read Clock Input: The read data output is synchronized with this clock. Read data output at the rising edge of the RCK cycle when /OE is pulled low (enabled). The internal read address pointer is incremented with this clock input.

/WE Write Enable Input: /WE controls the enabling/disabling of the data input. When /WE is pulled low, input data is acquired at the rising edge of the WCK cycle. When /WE is pulled high, the memory does not accept data input. The write address pointer is stopped at the current position. /WE signal is fetched at the rising edge of the WCK cycle.

/RE Read Enable Input: /RE controls the operation of the data output. When /RE is pulled low, output data is provided at the rising edge of the RCK cycle and the internal read address is incremented automatically. /RE signal is fetched at the rising edge of the RCK cycle.

/OE Output Enable Input: /OE controls the enabling/disabling of the data output. When /OE is pulled low, output data is provided at the rising edge of the RCK cycle. When /OE is pulled high, data output is disabled and the output pins remain at high impedance status. /OE signal is fetched at the rising edge of RCK cycle.

/WRST Write Reset Input: This reset signal initializes the write address to 0, and is fetched at the rising edge of the WCK input cycle.

/RRST Write Reset Input: This reset signal initializes the read address to 0, and is fetched at the rising edge of the RCK input cycle.

TST Test Pin: For testing purpose only. It should be pulled low for normal applications.

DEC: Decoupling cap pin, should be connected to a 1 μ F or 2.2 μ F capacitor to ground for 5V application. For 3.3V application, the DEC pin can be simply connected to the 3.3V power with regular 0.1 μ F bypass capacitor.

8.1 Memory Operation

Initialization

Apply /WRST and /RRST 0.1ms after power on, then follow the following instructions for normal operation.

Reset Operation

The reset signal can be given at any time regardless of the /WE, /RE and /OE status, however, they still need to meet the setup time and hold time requirements with reference to the clock input. When the reset signal is provided during disabled cycles, the reset operation is not executed until cycles are enabled again. After WRST and RRST signals are pulled low, the data output and input start from address 0.

Write Operation

Data input DI7~DI0 is written into the write register at the WCK input when /WE is pulled low. The write data should meet the setup time and hold time requirements with reference to the WCK input cycle.

Write operation is prohibited when /WE is pulled high, and the write address pointer is stopped at the current position. The write address starts from there when the /WE is pulled low again. The /WE signal needs to meet the setup time and hold time requirements with reference to the WCK input cycle.

Read Operation

Data output DO7~DO0 is written into the read register at the RCK input when both /RE and /OE are pulled low. The output data is ready after T_{AC} (access time) from the rising edge of the RCK input cycle.

The read address pointer is stopped at the current position when /RE is pulled high, and starts there when /RE is pulled low again.

/OE needs to be pulled low for read operations. When /OE is pulled high, the data outputs will be at high impedance stage. The read address pointer still increases synchronously with RCK regardless of the /OE status. The /RE and /OE signals need to meet the setup time and hold time requirements with reference to the RCK input cycle.

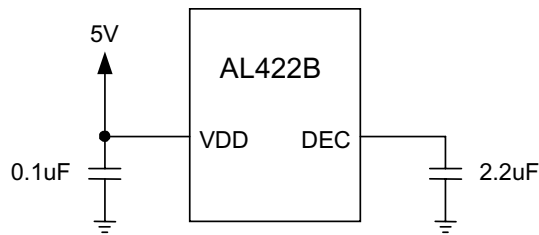
When the new data is read, the read address should be between 128 to 393,247 cycles after the write address, otherwise the output may not be new data.

8.2 5V and 3.3V applications

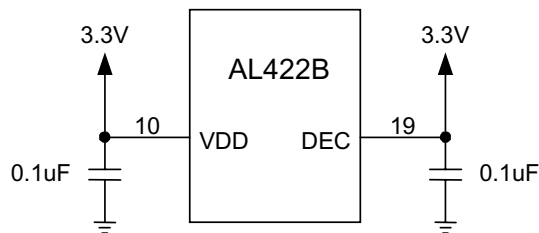
The AL422 can accept either 3.3V or 5V power with slightly different external configuration. The internal voltage regulator can convert 5V power to 3.3V for the embedded DRAM and logic circuitry when 5V power is applied to VDD pin (#10) only and leave the DEC pin (#19) decoupled by a capacitor of 1 μ F or 2.2 μ F to ground. The regulator can also be bypassed when 3.3V power is applied to both VDD and DEC pins. In either case the AL422 is 5V or 3.3V I/O tolerant. The 3.3V configuration consumes less power and is free from noise interference from the voltage regulator so may be more ideal for high-speed applications.

Please note that using the AL422B with 5V configuration can directly replace the previous AL422V5; using it with 3.3V configuration can directly replace the previous AL422V3. No additional modification is required.

The 5V configuration (direct replacement of the previous AL422V5) is as follows:



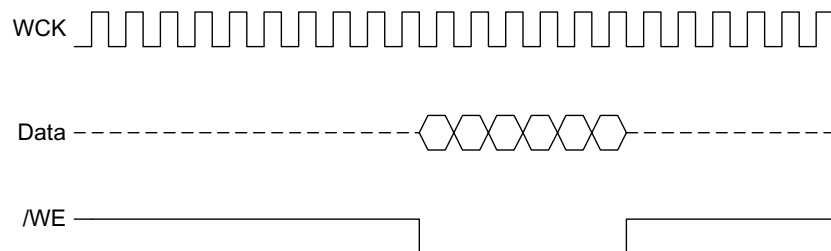
The 3.3V configuration (direct replacement of the previous AL422V3) is as follows:



8.3 Restrictions

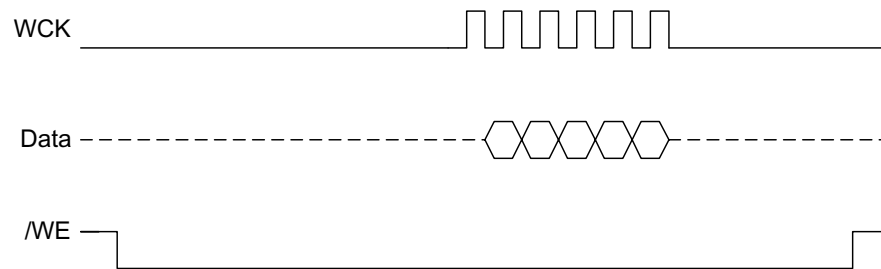
8.3.1 Irregular Read/Write

It is recommended that the WCK and RCK are kept running at least 1MHz at all times. The faster one of WCK and RCK is used as the DRAM refresh timing clock and has to be kept free running. When irregular FIFO I/O control is needed, keep the clock free running and use /WE or /RE to control the I/O as follows:



AL422-17 Slow Write - Correct

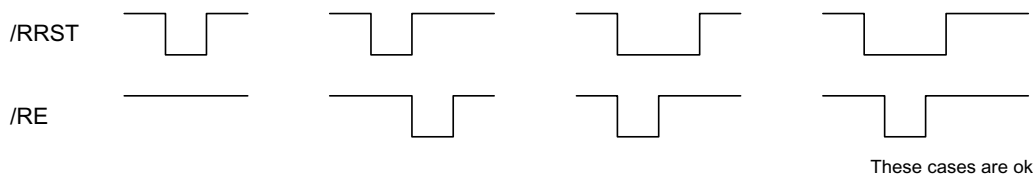
The following drawing shows irregular clock and should be avoided:



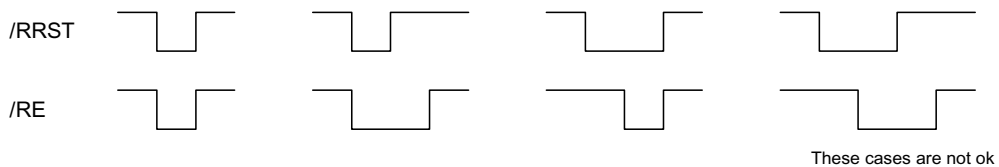
AL422-16 Slow Write - Incorrect

8.3.2 Read Enable during Reset Cycles

/RE should never be low at the rising edge of /RRST. The following cases are acceptable:



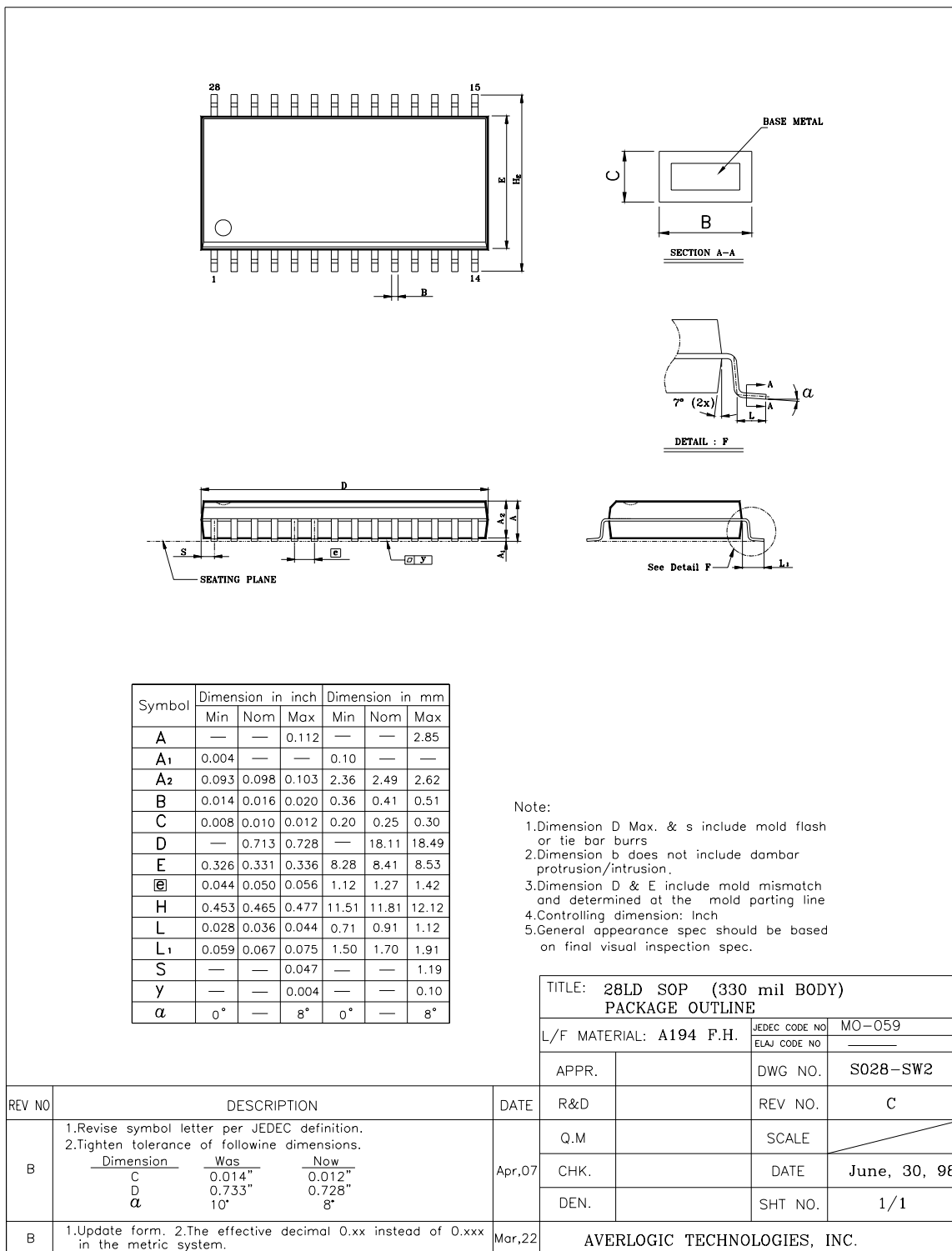
The following cases should always be avoided:



Please use the drawing AL422-14, Read Cycle Timing (RE, RRST) as enable/reset timing reference.

9.0 Mechanical Drawing

28 PIN PLASTIC SOP:



CONTACT INFORMATION

Averlogic Technologies Corp.
4F, No. 514, Sec. 2, Cheng Kung Rd., Nei-Hu Dist., Taipei, Taiwan
Tel: +886 2-27915050
Fax: +886 2-27912132
E-mail: sales@averlogic.com.tw
URL: <http://www.averlogic.com.tw>

Averlogic Technologies, Inc.
90 Great Oaks Blvd. #204, San Jose, CA 95119
USA
Tel: 1 408 361-0400
Fax: 1 408 361-0404
E-mail: sales@averlogic.com
URL: <http://www.averlogic.com>